

Title (en)

NANOSTRUCTURES WITH NEGATIVE DIFFERENTIAL RESISTANCE AND METHOD FOR MAKING SAME

Title (de)

NANOSTRUKTUREN MIT NEGATIVEM DIFFERENTIELLEM WIDERSTAND UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

NANOSTRUCTURES A RESISTANCE DIFFERENTIELLE NEGATIVE ET LEUR PROCEDE DE FABRICATION

Publication

EP 1897145 A1 20080312 (FR)

Application

EP 06777518 A 20060629

Priority

- EP 2006063692 W 20060629
- FR 0551848 A 20050630
- FR 0650145 A 20060116

Abstract (en)

[origin: WO2007003576A1] The invention concerns nanostructures of 0, 1, 2 and 3 dimensions, with negative differential resistance and a method for making said nanostructures. The inventive nanostructure is in particular useful in nanoelectronics. It comprises at least one structure (32) or at least a plurality of said at least one structure, on the surface of a silicon carbide substrate (30), the structure being selected among quantum connection pads, atomic segments, atomic lines and aggregates, and at least one metal deposit (34), said metal deposit covering at least the structure or at least the plurality of said at least one structure, or the combination of at least two of said structures with 0, 1, 2 or 3 dimensions.

IPC 8 full level

H01L 29/12 (2006.01); **H01L 29/861** (2006.01)

CPC (source: EP US)

B82Y 10/00 (2013.01 - EP US); **H01L 29/045** (2013.01 - EP US); **H01L 29/125** (2013.01 - EP US); **H01L 29/127** (2013.01 - EP US); **H01L 29/861** (2013.01 - EP US); **H01L 29/1608** (2013.01 - EP US)

Citation (search report)

See references of WO 2007003576A1

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

WO 2007003576 A1 20070111; EP 1897145 A1 20080312; JP 2009500815 A 20090108; US 2010072472 A1 20100325

DOCDB simple family (application)

EP 2006063692 W 20060629; EP 06777518 A 20060629; JP 2008518850 A 20060629; US 92297006 A 20060629